

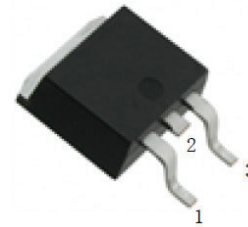
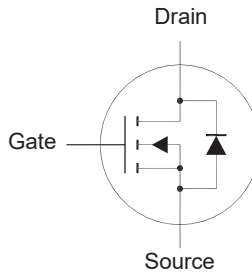
N-Channel Enhancement Mode MOSFET

Features

- Surface-mounted package
- Halogen and Antimony Free(HAF)
RoHS compliant

Applications

- Load switch
- PWM applications
- LCD TV CCFL inverter



1.Gate 2.Drain 3.Source
TO-252 Plastic Package

Key Parameters

Parameter	Value	Unit
BV_{DSS}	65	V
$R_{DS(ON)}$ Max	11 @ $V_{GS} = 10$ V	m Ω
	16 @ $V_{GS} = 4.5$ V	
$V_{GS(th)}$ typ	1.7	V
Q_g typ	14 @ $V_{GS} = 10$ V	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	48	A
		30	
	$T_c = 25^\circ\text{C}$		
	$T_c = 100^\circ\text{C}$		
Peak Drain Current Pulsed ¹⁾	I_{DM}	160	A
Power Dissipation	P_D	41.7	W
	$T_c = 25^\circ\text{C}$		
Avalanche Current	I_{AS}	12	A
Single Pulse Avalanche Energy ²⁾	E_{AS}	36	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	3	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	50	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width ≤ 100 μs , Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.5$ mH, $R_g = 25$ Ω , $I_{AS} = 12$ A, $V_{GS} = 10$ V.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at T_a = 25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at I _D = 250 μA	BV _{DSS}	65	-	-	V
Drain-Source Leakage Current at V _{DS} = 52 V	I _{DSS}	-	-	1	μA
Gate-Source Leakage Current at V _{GS} = ± 20 V	I _{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at V _{DS} = V _{GS} , I _D = 250 μA	V _{GS(th)}	1.2	-	2.5	V
Drain-Source On-State Resistance at V _{GS} = 10 V, I _D = 10 A at V _{GS} = 4.5 V, I _D = 8 A	R _{DS(on)}	- -	8.5 -	11 16	mΩ
DYNAMIC PARAMETERS					
Forward Transconductance at V _{DS} = 5 V, I _D = 5 A	g _{fs}	-	13	-	S
Gate resistance at V _{DS} = 0 V, V _{GS} = 0 V, f = 1 MHz	R _g	-	2	-	Ω
Input Capacitance at V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz	C _{iss}	-	825	-	pF
Output Capacitance at V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz	C _{oss}	-	290	-	pF
Reverse Transfer Capacitance at V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz	C _{rss}	-	15	-	pF
Gate charge total at V _{DS} = 30 V, I _D = 10 A, V _{GS} = 10 V at V _{DS} = 30 V, I _D = 10 A, V _{GS} = 4.5 V	Q _g	- -	14 7.2	- -	nC
Gate to Source Charge at V _{DS} = 30 V, I _D = 10 A, V _{GS} = 10 V	Q _{gs}	-	2.6	-	nC
Gate to Drain Charge at V _{DS} = 30 V, I _D = 10 A, V _{GS} = 10 V	Q _{gd}	-	2.8	-	nC
Turn-On Delay Time at V _{DS} = 30 V, I _D = 10 A, V _{GS} = 10 V, R _g = 4.7 Ω	t _{d(on)}	-	10	-	ns
Turn-On Rise Time at V _{DS} = 30 V, I _D = 10 A, V _{GS} = 10 V, R _g = 4.7 Ω	t _r	-	16	-	ns
Turn-Off Delay Time at V _{DS} = 30 V, I _D = 10 A, V _{GS} = 10 V, R _g = 4.7 Ω	t _{d(off)}	-	9	-	ns
Turn-Off Fall Time at V _{DS} = 30 V, I _D = 10 A, V _{GS} = 10 V, R _g = 4.7 Ω	t _f	-	2	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at I _S = 1 A, V _{GS} = 0 V	V _{SD}	-	-	1.2	V
Body-Diode Continuous Current	I _S	-	-	48	A
Body-Diode Continuous Current, Pulsed	I _{SM}	-	-	160	A
Body Diode Reverse Recovery Time at I _S = 10 A, di/dt = 100 A / μs	t _{rr}	-	17	-	ns
Body Diode Reverse Recovery Charge at I _S = 10 A, di/dt = 100 A / μs	Q _{rr}	-	6.5	-	nc

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

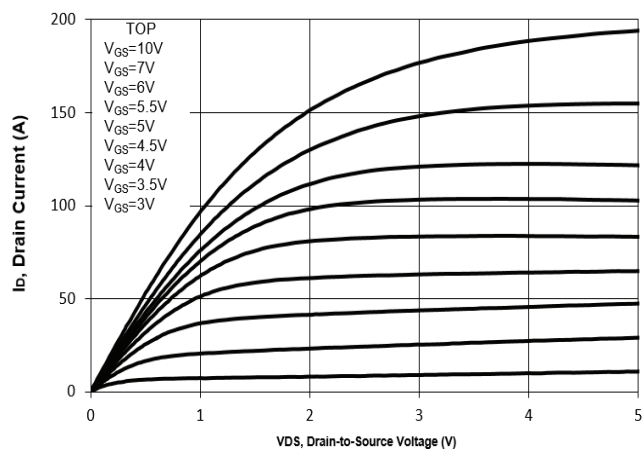


Fig. 2 Typical Transfer Characteristics

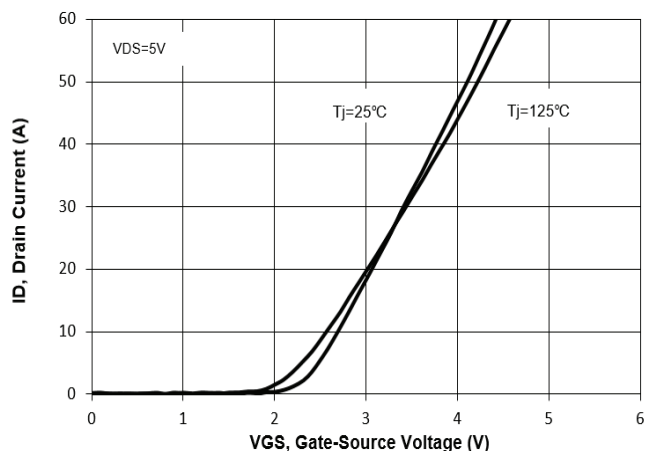


Fig. 3 on-Resistance vs. Drain Current

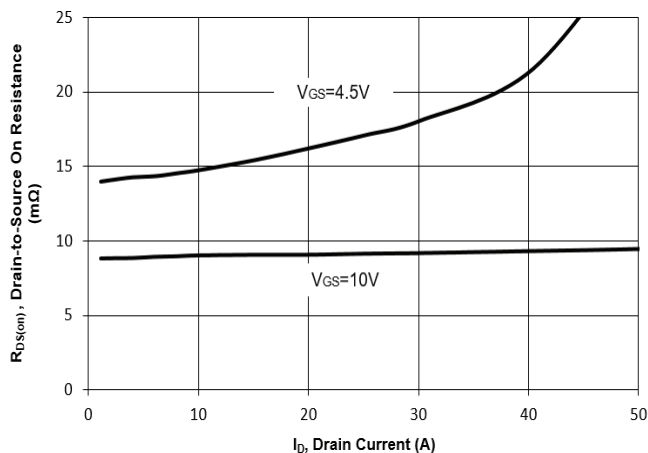


Fig. 4 on-Resistance vs. Gate to Source Voltage

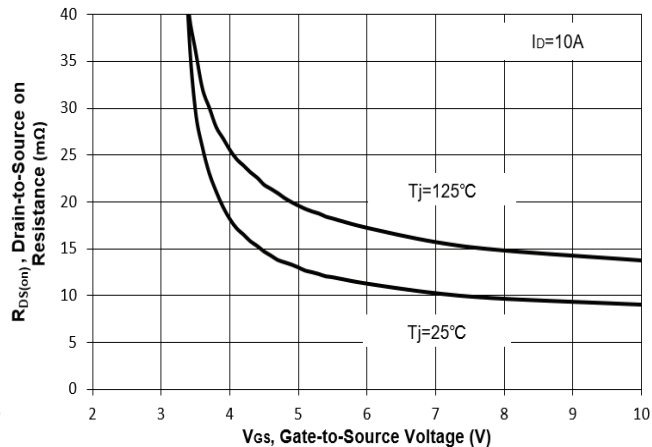


Fig. 5 on-Resistance vs. TJ

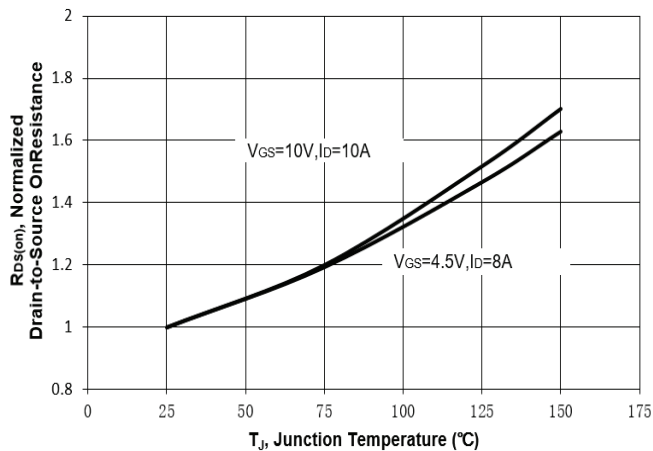


Fig. 6 Typical Body-Diode Forward Characteristics

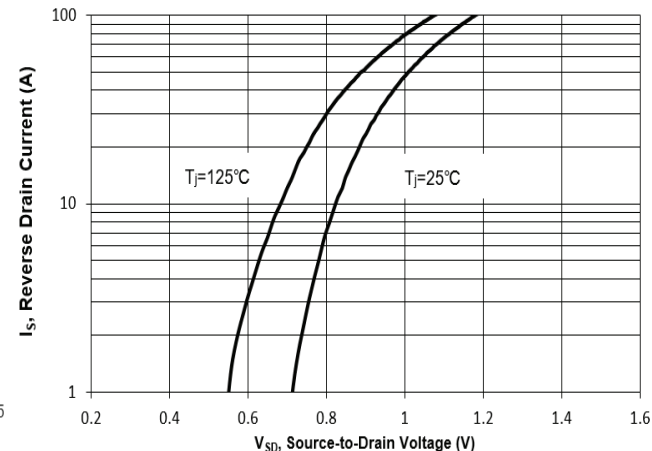


Fig. 7 Typical Junction Capacitance

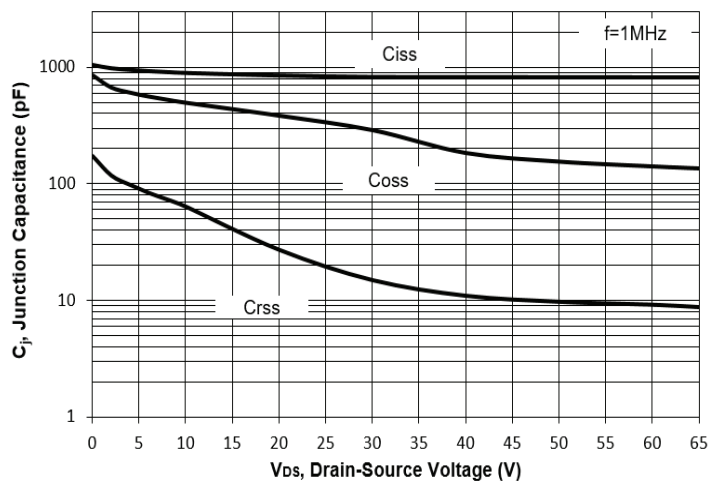


Fig. 8 Drain-Source Leakage Current vs. T_J

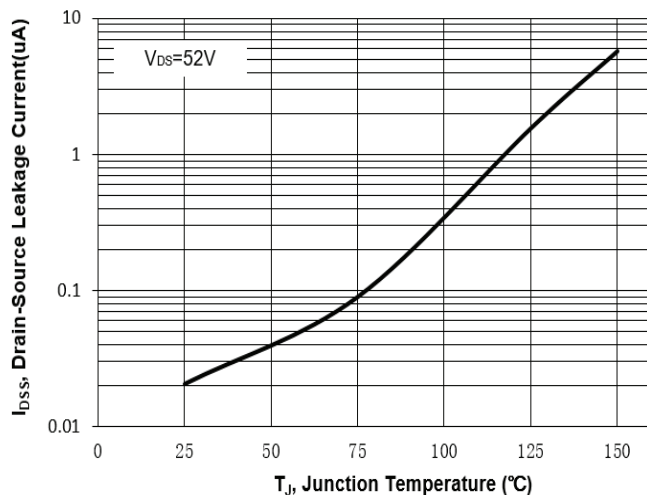


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

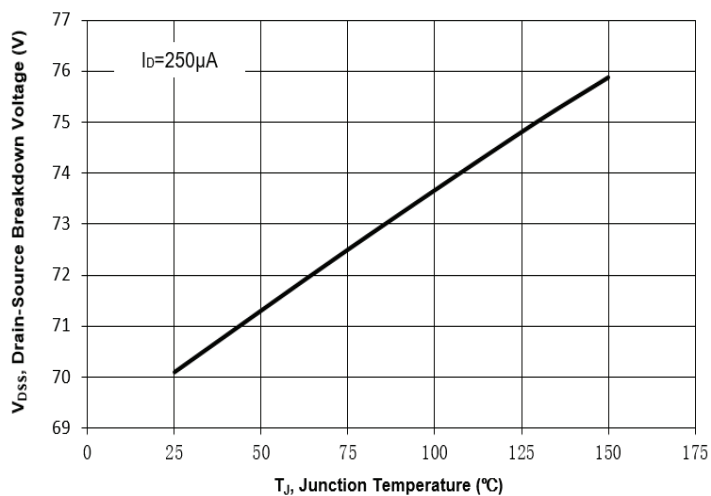


Fig. 10 Gate Threshold Variation vs. T_J

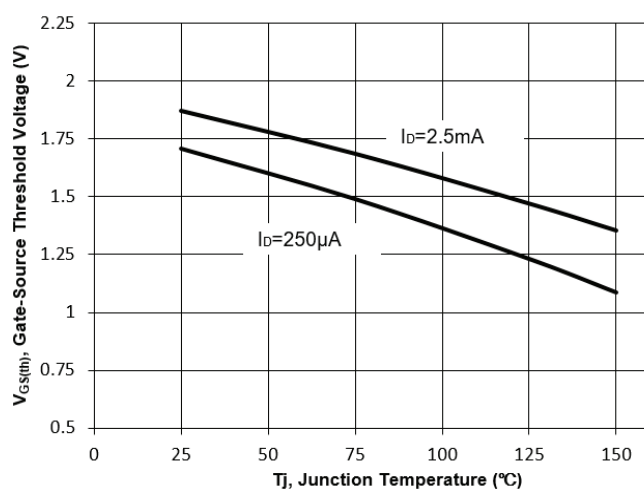


Fig. 11 Gate Charge

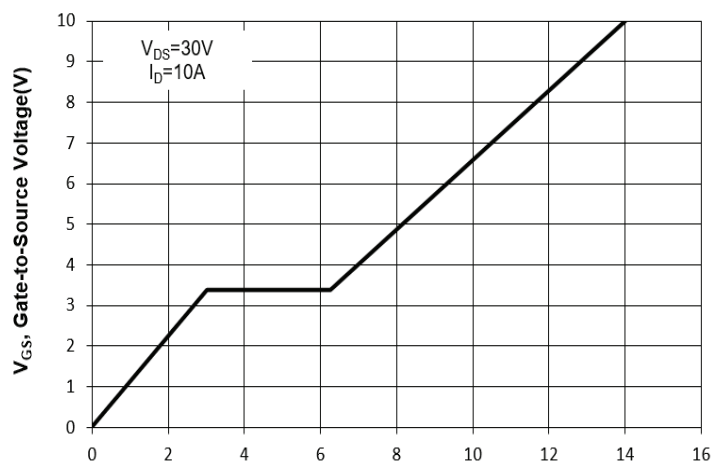
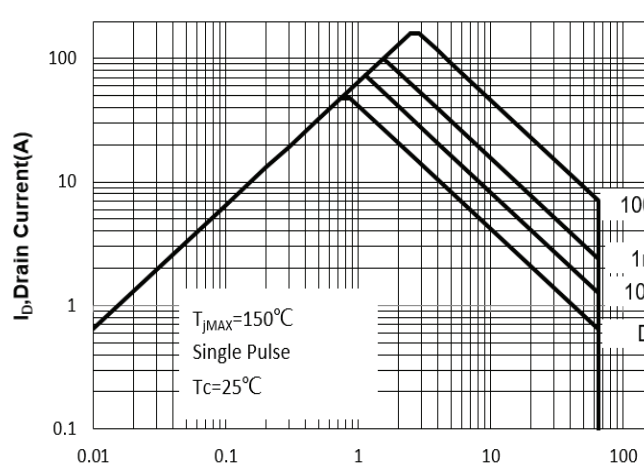


Fig. 12 Safe Operation Area



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)

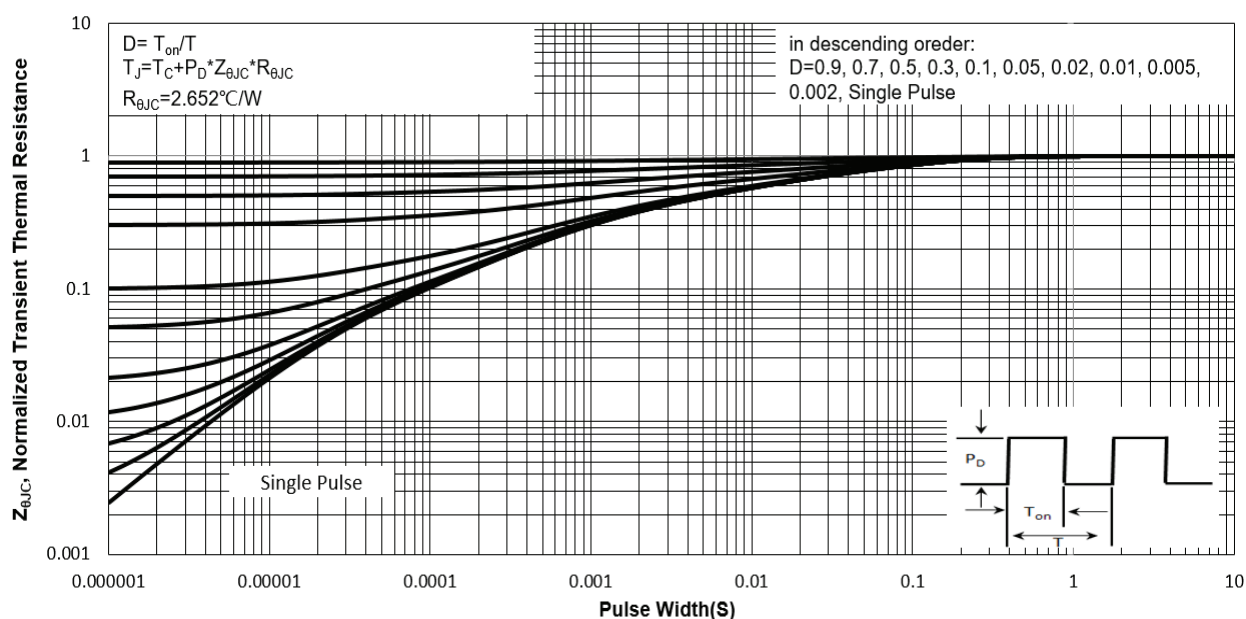
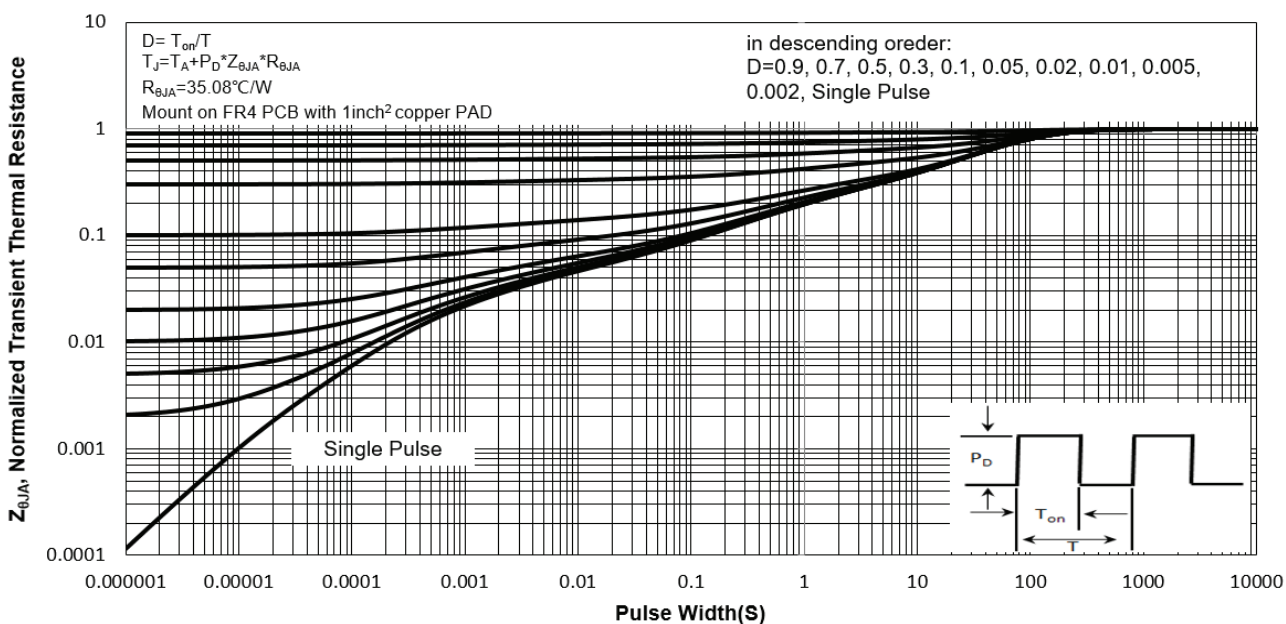


Fig. 14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)



Test Circuits

Fig.1-1 Switching times test circuit

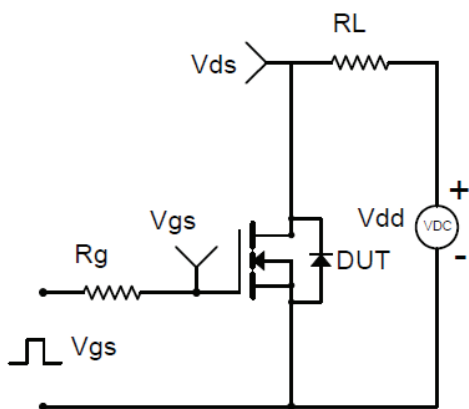


Fig.1-2 Switching Waveform

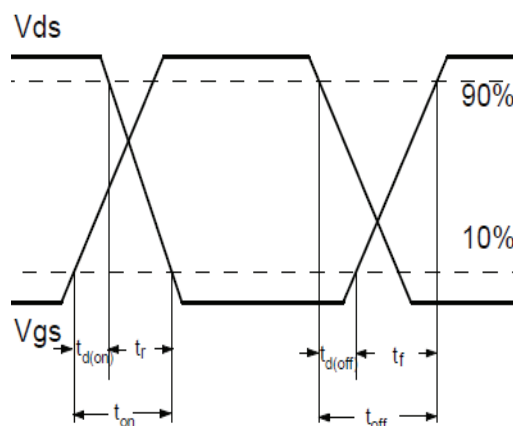


Fig.2-1 Gate charge test circuit

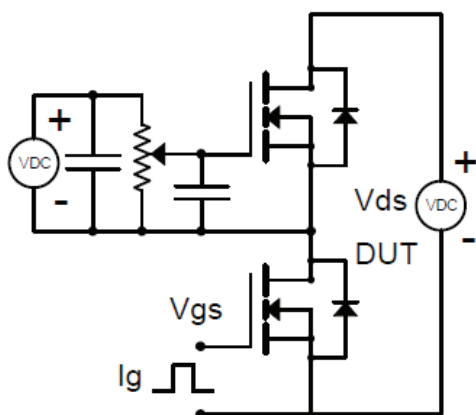


Fig.2-2 Gate charge waveform

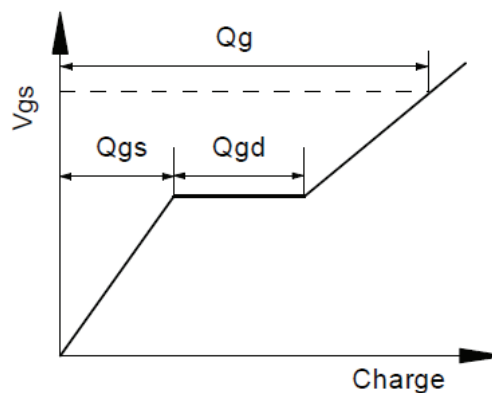


Fig.3-1 Avalanche test circuit

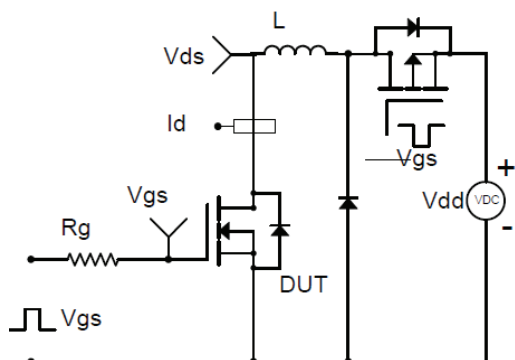
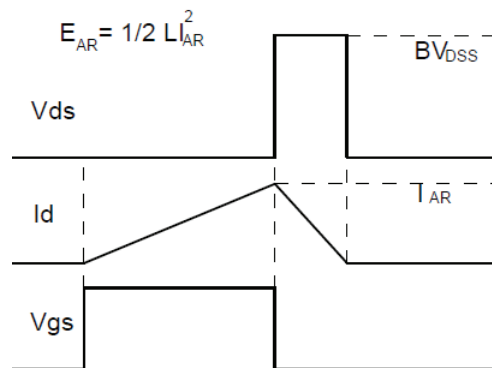
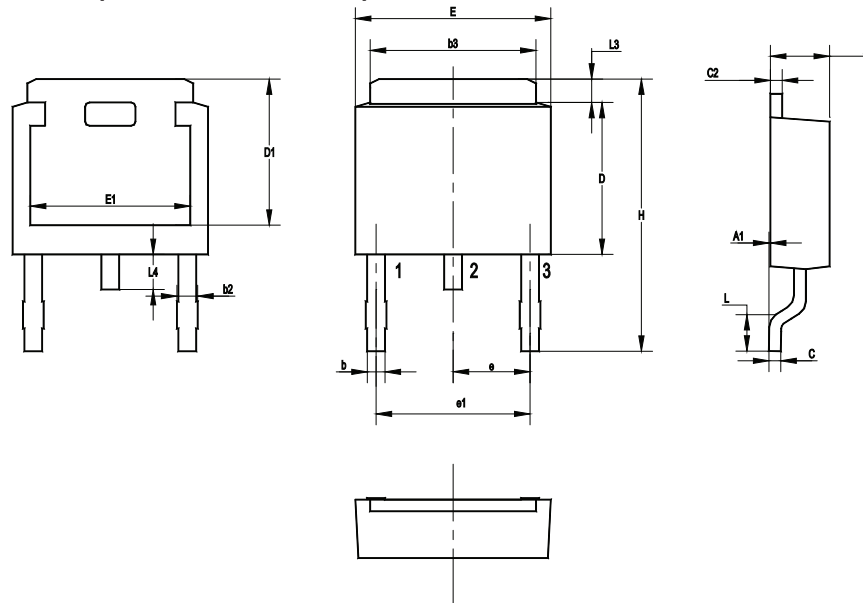
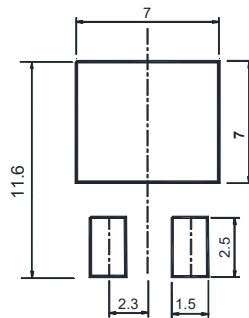


Fig.3-2 Avalanche waveform



Package Outline (Dimensions in mm)
TO-252


UNIT	A	A1	b	b2	b3	C	C2	D	D1	E	E1	e	e1	H	L	L3	L4
mm	2.5	0.15	1.0	1.15	5.5	0.65	0.65	6.2	5.4	6.7	5.0	2.30	4.60	10.7	1.78	1.20	1.10
	2.1	0	0.5	0.65	4.9	0.4	0.4	5.6	5.0	6.1	4.6	TYP.	TYP.	9	1.40	0.85	0.51

Recommended Soldering Footprint

Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-252	16	8 ± 0.1	0.315 ± 0.004	330	13	2,500

Marking information

" DRE6N110LS " = Part No.

" ***** " = Date Code Marking

Font type: Arial



Disclaimer: Our company reserve the right to make modifications, enhancements, improvements, corrections or other changes to improve product design, functions and reliability, anytime without notice.